

MPSA194

PNP SILICON TRANSISTOR

PNP EPITAXIAL SILICON TRANSISTOR

DESCRIPTION

The UTC **MPSA194** is designed for high voltage low power switching applications especially for use in telephone and telecommunication circuits.

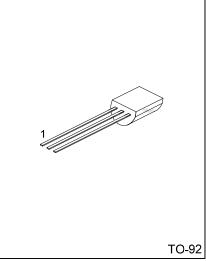
FEATURES

- * Collector-Emitter Voltage: V_{CEO}=400V
- * Power Dissipation: 1.0W

APPLICATIONS

- * Telephone Circuit
- * Telecommunication Circuit

ORDERING INFORMATION



Lead-free: MPSA194L Halogen-free: MPSA194G

Ordering Number			Dookogo	Pin Assignment			Deelvine	
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
MPSA194-T92-B	MPSA194L-T92-B	MPSA194G-T92-B	TO-92	Е	В	С	Tape Box	
MPSA194-T92-K	MPSA194L-T92-K	MPSA194G-T92-K	TO-92	Е	В	С	Bulk	

MPSA194L- <u>T92-</u> B	(1)Packing Type	(1) B: Tape Box, K: Bulk,
	(2)Package Type (3)Lead Plating	(2) T92: TO-92 (3) G: Halogen Free, L: Lead Free, Blank: Pb/Sn

■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Collector to Base Voltage	V _{CBO}	-400	V	
Collector to Emitter Voltage	V _{CEO}	-400	V	
Emitter to Base Voltage	V _{EBO}	-6	V	
Collector Current	Ι _C	-800	mA	
Collector Dissipation (Ta=25°C)	Pc	1.0	W	
Junction Temperature	TJ	150	°C	
Storage Temperature	T _{STG}	-55 ~ +150	°C	

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

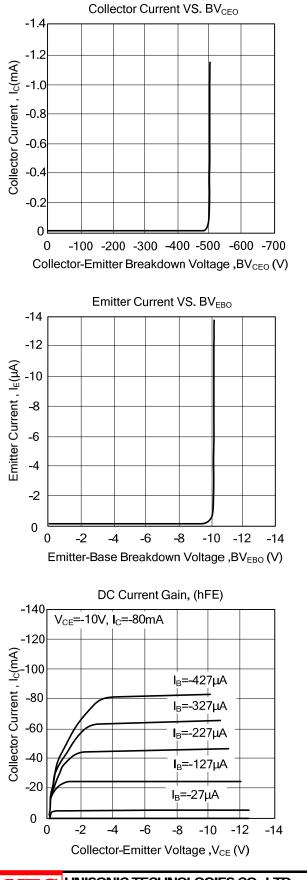
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	I _C =-100μA, I _E =0A	-400			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	$I_{\rm C}$ =-1mA, $I_{\rm B}$ =0A	-400			V
Collect Cut-off Current	I _{CBO}	V _{CB} =-400 V, I _E =0A			-10	μA
Collect Cut-off Current	I _{CEO}	V _{CB} =-200 V, V _{BE} =0V			-1	μA
Emitter Cut-off Current	I _{EBO}	$V_{EB} = -6 V, I_{C} = 0A$			-0.2	μA
		V _{CE} =-10 V ,I _C =-1mA	50			
DC Current Gain	h _{FE}	V _{CE} =-10 V ,I _C =-20mA	50		800	
		V _{CE} =-10 V ,I _C =-80mA	40			
Base-Emitter Saturation Voltage	V _{BE(SAT)}	I _C =-20mA, I _B =- 2mA			-0.9	V
	V	I _C =-20mA, I _B =- 4mA			-0.2	V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =-80mA, I _B =- 2mA			-1.2	V
Output Capacitance	C _{OB}	V _{CB} =-20 V, I _E =0A, f =1MHz			30	pF
Current Gain Bandwidth Product	f⊤	$V_{CE} = -20V$, $I_{E} = -10A$, f =1MHz	10			MH_Z

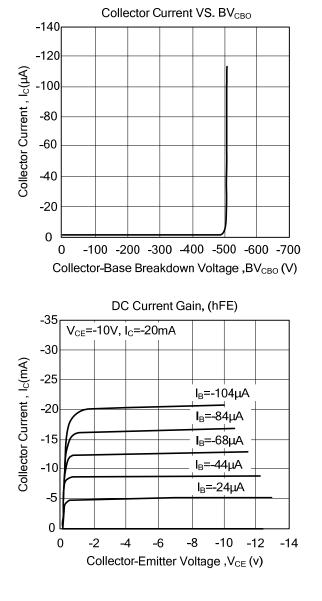


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TYPICAL CHARACTERISTICS





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